

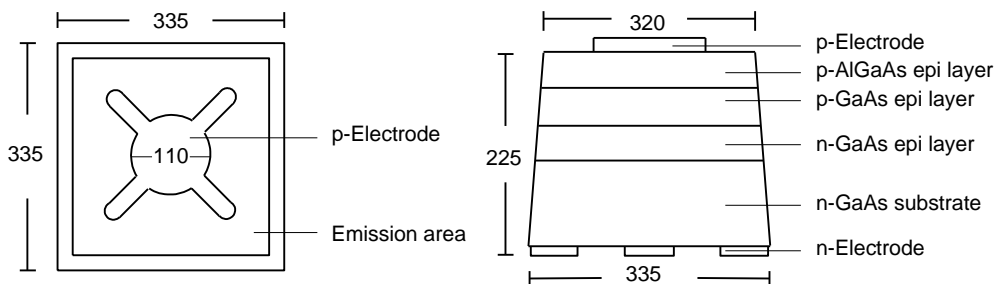
■ Features :

- AlGaAs/GaAs Wafer
- Good Spectral Matched to Si Detector
- High Power
- Low Forward Voltage

■ Typical Applications :

- Remote Controller
- Peripherals
- Photo Coupler
- Photo Interrupter

■ Outline Dimensions : (Unit: μm)



■ Physical Structure :

Chip dimension	Chip size	335 μm x 335 μm
	Thickness	225 μm
	Emission area	320 μm
	Bonding pad	110 μm
Electrode	Top: P (anode)	Gold
	Backside: N (cathode)	Gold alloy
Surface condition	Frosted	

■ Electro-Optical Characteristics : ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 100 \text{ mA}$	-	1.34	1.50	V
		$I_F = 200 \text{ mA}$	-	1.47	1.65	
Reverse Voltage	V_R	$I_R = 10 \text{ uA}$	5	-	-	V
Wavelength	λ_p	$I_F = 20 \text{ mA}$	-	940	-	nm
Spectral width at half height	$\Delta\lambda$	$I_F = 20 \text{ mA}$	-	50	-	nm
Radiant Power	P_o	$I_F = 20 \text{ mA}$	0.90	1.10	-	mW

※ ED-014IRA-T is not suitable for package of electrical white board application without adding soft gel. OPTOTECH suggests applying ED-E14IRA for electrical white board application.

■ Typical Electro-Optical Characteristics Curve:

Fig 1. Forward Current vs. DC Forward Voltage

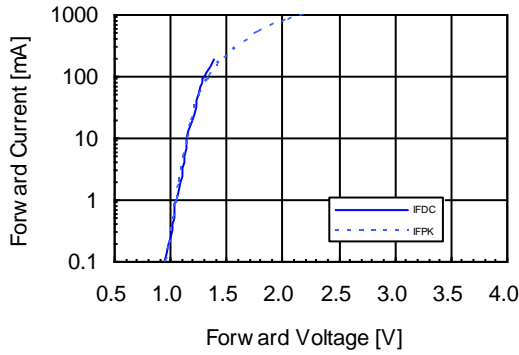


Fig 2. Relative Radian Power vs. Wavelength

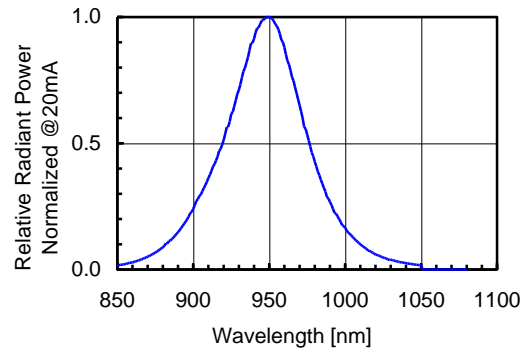


Fig 3. Relative Radian Power vs. Forward DC Current

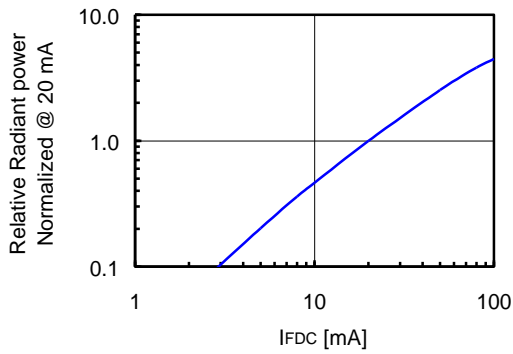


Fig 4. Relative Radian Power vs. Forward Peak Current

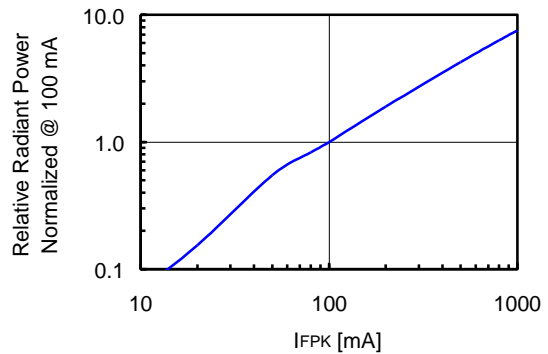


Fig 5. Forward DC Voltage vs. Temperature

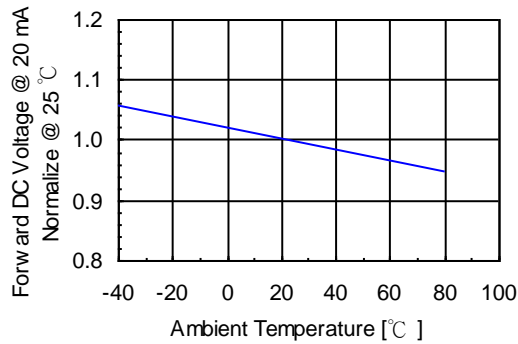


Fig 6. Relative Radian Power vs. Temperature

